

ABSTRACT

A high performance semiconductor device that can realize surface protection and surface inactivation and is fabricated using a film formation method and technique that enable improvement of high frequency characteristics, and an electronic device for a communication system including the semiconductor device, are provided.

The semiconductor device is characterized in that a film having boron, carbon, and nitrogen as main components and to which sulfur is added serves as a surface protection film, and at least part of a surface is covered.